



(19)

(11) Publication number:

63102225 A

Generated Document

PATENT ABSTRACTS OF JAPAN

(21) Application number: 61247678

(51) Intl. Cl.: H01L 21/22 H01L 21/68

(22) Application date: 20.10.86

(30) Priority:

(43) Date of application publication: 07.05.88

(84) Designated contracting states:

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(54) WAFER BOAT FOR VERTICAL TYPE SEMICONDUCTOR THERMAL TREATMENT EQUIPMENT

(57) Abstract:

PURPOSE: To prevent the effect of the turbulent flow region of a reaction gas generated in sections adjacent to connecting bars, and to equalize film thickness by erecting a plate, in which a wafer is housed into space with a recessed section slightly larger than the diameter of the wafer, between the connecting bars and separating the wafer from the connecting bars.

CONSTITUTION: Upper and lower end plates 12, 14 are connected by connecting 16 e.g. six in a wafer boat 10. A plate 20 is erected onto a large number of notches 18 shaped separate in the axial direction of each connecting bar 16. The plate 20 has a ring 22 on a plate body 21, and the diameter and depth of a recessed section 23 in the ring 22 are formed in size slightly larger than a wafer. Consequently, since the periphery of the wafer is positioned separately by from the connecting bars 16 considerably, the effect of a reaction gas changed into turbulent flows generated in sections adjacent to the connecting bars is reduced. Since the circumferential surface of the wafer 24 is also exposed to the reaction gas having a normal flow in the same manner as the center, the equalization of the film thickness the periphery and the center is promoted.

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